

--A SEMICONDUCTOR DEVICE HAVING AT LEAST ONE SOURCE/DRAIN REGION FORMED ON AN ISOLATION REGION AND A METHOD OF MANUFACTURE THEREFOR--

IN THE CLAIMS

(1) Kindly rewrite Claim 1 as follows:

Sub B1 >

1. (Amended) A semiconductor device, comprising:
a semiconductor substrate;
a gate formed above the semiconductor substrate;
an isolation region located within a trench formed in the semiconductor substrate;
at least a portion of one of a source/drain region formed on the isolation region, but not
in the semiconductor substrate.

(2) Kindly rewrite Claim 7 as follows:

Sub B3 >

7. (Amended) A semiconductor device, comprising:
a channel region located in a semiconductor substrate;
a trench located adjacent a side of the channel region;
an isolation region located in the trench; and
at least a portion of one of a source/drain region located on the isolation region, but not
in the semiconductor substrate.

(3) Kindly rewrite Claim 12 as follows:

Sub B5 >

12. (Amended) A semiconductor device, comprising:

~~a channel region located in a semiconductor substrate;~~
~~an isolation region located adjacent the channel region, the isolation region being located~~
~~within a trench formed in the semiconductor substrate and not extending under the channel region;~~
and
~~source/drain regions having a first portion located in the semiconductor substrate and a~~
~~second portion located on the isolation region, but not in the semiconductor substrate.~~

*a³
Cancelled*

(4) Kindly rewrite Claim 17 as follows:

Sub B6 >
17. (Amended) A semiconductor device, comprising:
a first transistor located adjacent a second transistor, wherein both the first and second
transistors are located over a semiconductor substrate;
a⁴
an isolation region located between the first and second transistors and within a trench
located within the semiconductor substrate; and
source/drain regions associated with each of the first and second transistors, each of the
source/drain regions having a first portion located in the semiconductor substrate and a second
portion located on the isolation region, but not in the semiconductor substrate.

(5) Kindly rewrite Claim 21 as follows:

Sub B7 >
21. (Amended) A method of manufacturing a semiconductor device, comprising:
a⁵
providing a semiconductor substrate;
creating a gate above the semiconductor substrate;
forming an isolation region within a trench located in the semiconductor substrate;

~~forming at least a portion of one of a source/drain region above the isolation region, but not in the semiconductor substrate.~~

(6) Kindly rewrite Claim 22 as follows:

A⁵
Canceled

22. (Amended) The method as recited in Claim 21 wherein forming an isolation region includes forming an isolation region adjacent to the semiconductor substrate.

(7) Kindly rewrite Claim 27 as follows:

SUB B9 >

A⁶

27. (Amended) An integrated circuit, comprising:
semiconductor devices, including;
a semiconductor substrate;
a gate formed above the semiconductor substrate;
an isolation region located within a trench formed in the semiconductor substrate;
at least a portion of one of a source/drain region formed above the isolation region,
but not in the semiconductor substrate; and
interconnect structures contacting the semiconductor devices.

(8) Kindly cancel Claim 33 without prejudice or disclaimer.